

Figure 2B is a top schematic view of another embodiment of an apparatus containing a capping module and high pressure deposition module of the present invention;

Figure 3A is a top schematic planar view of one embodiment of a capping module and high pressure deposition module of the present invention;

Figure 3B is a top schematic view of one embodiment of a capping module and high pressure deposition module of the present invention;

Figure 4 is a perspective view of an embodiment of a loadlock chamber of the present invention;

Figure 5 is a top schematic view of a transfer chamber and a processing chamber showing a substrate handling member of the present invention mounted in the transfer chamber and in a retracted position ready for rotation within the transfer chamber or extension into another chamber;

Figure 6 is a top schematic view of a transfer chamber and a processing chamber showing a substrate handling member of the present invention mounted in the transfer chamber and in an extended position wherein the blades are positioned in the processing chamber;

Figure 7 is a cross sectional view of a rapid thermal anneal chamber;

Figure 8 is a perspective view of one embodiment of a PECVD chamber included in the capping module of the present invention;

Figure 9 is a cross sectional view of the PECVD chamber of the present invention;

Figure 10 is an exploded view of the gas distribution assembly for the PECVD chamber;

Figure 11 is a top view of a PECVD chamber of the present invention with the lid removed;

Figure 12 is an illustrative block diagram of the hierarchical control structure of a computer program for process control;

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Figure 13 is an illustrative view of the mesoporous film process showing cubic phase structure and mesoporous film structure;

Figure 14 is a cross sectional view showing a dual damascene structure comprising a low k silicon oxide layer and capping layer of the present invention; and

Figures 15A-H are cross sectional views showing a dual damascene deposition sequence of the present inventions. --

REMARKS

Further to our Amended Response to Restriction Requirement and Preliminary Amendment mailed May 8, 2002, Applicants have amended the specification from page 7, line 19 through page 8, line 24 as requested by the Examiner.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "Version with Markings to Show Changes Made."

CONCLUSION

In view of the foregoing, Applicants believe all claims now pending in this Application are in condition for allowance. The issuance of a formal Notice of Allowance at an early date is respectfully requested.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 925-472-5000.

Respectfully submitted,

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